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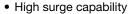
Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 70 A

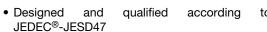


PRIMARY CHARACTERISTICS			
I _{T(AV)}	70 A		
V_{DRM}/V_{RRM}	1200 V, 1600 V		
V_{TM}	1.25 V		
I _{GT}	100 mA		
T_J	-40 °C to +125 °C		
Package	Super TO-247		
Circuit configuration	Single SCR		

FEATURES







RoHS

 Material categorization: for definitions of compliant compliance please see www.vishav.com/doc?99912

APPLICATIONS

- AC switches
- High voltage input rectification (soft start)
- · High current crow-bar
- Other phase-control circuits
- Designed to be used with Vishay input diodes, switches, and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-70TPS..PbF high voltage series of silicon controlled rectifiers are specifically designed for high and medium power switching, and phase control applications.

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	70	۸		
I _{RMS}	Lead current limitation	75	Α		
V _{RRM} /V _{DRM}	Range	1200 to 1600	V		
I _{TSM}		1100	Α		
V _T	100 A, T _J = 25 °C	1.4	V		
dV/dt		500	V/µs		
dl/dt		150	A/µs		
TJ		-40 to +125	°C		

VOLTAGE RATINGS					
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA		
VS-70TPS12PbF	1200	1300	15		
VS-70TPS16PbF	1600	1700	15		



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PARAMETER	SYMBOL	Т	TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	T _C = 82 °C, 180° cor	nduction half sine wave		70	
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}	Lead current limitation	Lead current limitation		75	А
Maximum peak, one-cycle	L	10 ms sine pulse, rat	ted V _{RRM} applied		930	
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no	voltage reapplied	Lorent T	1100	
Maximum 12t for fusing	I ² t	10 ms sine pulse, rat	ted V _{RRM} applied	Initial T _J = T _J maximum	4325	A ² s
Maximum I ² t for fusing	I-ι	10 ms sine pulse, no	10 ms sine pulse, no voltage reapplied			A-S
Maximum l ² √t for fusing	I²√t	t = 0.1 ms to 10 ms,	t = 0.1 ms to 10 ms, no voltage reapplied		61 150	A²√s
Low level value of threshold voltage	V _{T(TO)1}			0.916	V	
High level value of threshold voltage	V _{T(TO)2}	T _{.1} = 125 °C		1.21] V	
Low level value of on-state slope resistance	r _{t1}	1J= 125 C		4.138	m 0	
High level value of on-state slope resistance	r _{t2}			3.43	mΩ	
Maximum peak on-state voltage	V_{TM}	100 A, T _J = 25 °C			1.4	V
Maximum rate of rise of turned-on current	dl/dt	T _J = 25 °C		150	A/μs	
Maximum holding current	I _H	Anode supply = 6 V, resistive load, initial I _T = 1 A, T _J = 25 °C		200		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		400	A	
Maximum reverse and direct leakage current	I _{RRM} /I _{DRM}	T _J = 25 °C	$V_R = \text{rated } V_{RRM} / V_{DR}$	M	1.0	mA
		T _J = 125 °C	$(T_J = T_J \text{ max., linear})$	to 80 %	15	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = 125 ^{\circ}\text{C}$ $V_{DRM} = R_g - k = \text{open}$		500	V/µs	

TRIGGERING					
PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	T = 30 µs		10	W
Maximum average gate power	P _{G(AV)}	ι = 30 μs		2.5	VV
Maximum peak gate current	I _{GM}			2.5	Α
Maximum peak negative gate voltage	- V _{GM}			10	
		T _J = - 40 °C		1.8	V
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	1.5	V
		T _J = 125 °C		1.1	
		T _J = - 40 °C		150	
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	100	mA
		T _J = 125 °C		80	
Maximum DC gate voltage not to trigger	V_{GD}	T = 105 °C \/ = reted value		0.25	V
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = rated value		6	mA

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THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER		SYMBOL TEST CONDITIONS		VALUES	UNITS	
Maximum junction temperature	range	TJ		-40 to +125	°C	
Maximum storage temperature	range	T _{Stg}		-40 to +150		
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	0.27		
Maximum thermal resistance, junction to ambient		R_{thJA}		40	°C/W	
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.2		
Approximate weight				6	g	
Approximate weight				0.21	oz.	
Mounting torque ——	minimum			6 (5)	kgf · cm	
	maximum			12 (10)	(lbf · in)	
Marking device			Casa atula Supar TO 247	70TPS	12	
			Case style Super TO-247	70TPS	70TPS16	

△R _{thJ-hs} CONDUCTION PER JUNCTION											
DEVICE	S	SINE HALF WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION				UNITS
DEVICE	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VS-70TPSPbF	0.078	0.092	0.117	0.172	0.302	0.053	0.092	0.125	0.180	0.306	°C/W

Note

The table above shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC

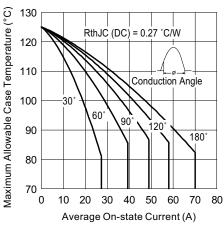


Fig. 1 - Current Rating Characteristics

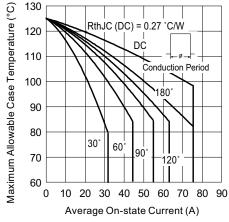


Fig. 2 - Current Rating Characteristics



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At any rated load condition and with

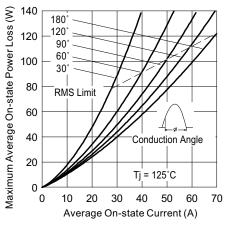
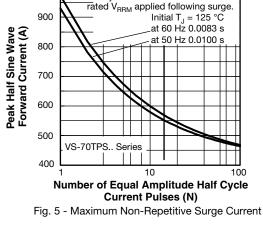


Fig. 3 - On-State Power Loss Characteristics



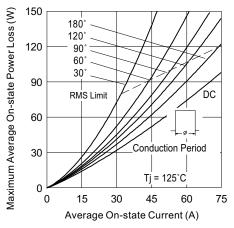


Fig. 4 - On-State Power Loss Characteristics

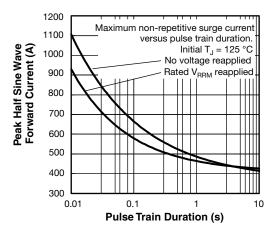


Fig. 6 - Maximum Non-Repetitive Surge Current

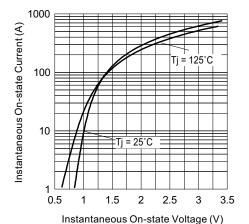
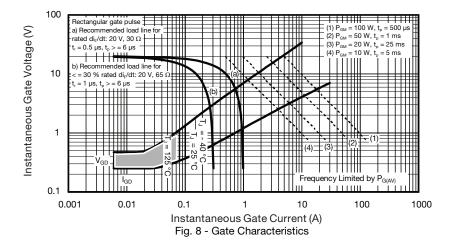


Fig. 7 - On-State Voltage Drop Characteristics

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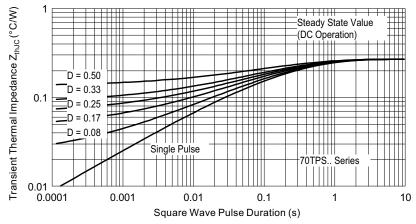
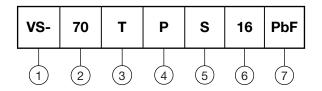


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE





1 - Vishay Semiconductors product

2 - Current rating (70 = 70 A)

3 - Circuit configuration:

T = thyristor

4 - Package:

P = super TO-247

5 - Type of silicon:

S = standard recovery rectifier

12 = 1200 V 16 = 1600 V

6 - Voltage code x 100 = V_{RRM}

7 - PbF = lead (Pb)-free

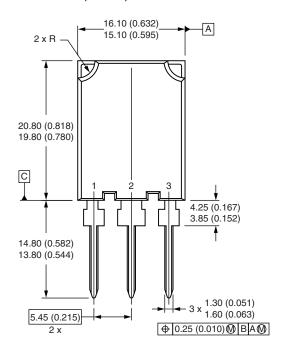
ORDERING INFORMATION (example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-70TPS12PbF	25	500	Antistatic plastic tube		
VS-70TPS16PbF	25	500	Antistatic plastic tube		

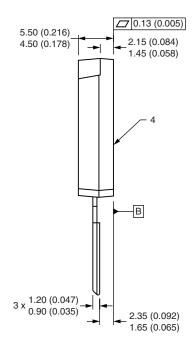
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95073</u>				
Part marking information	www.vishay.com/doc?95070			

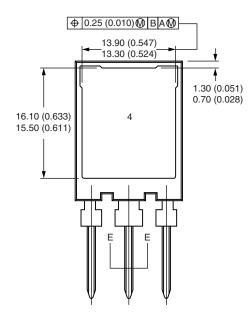
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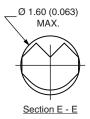
Super TO-247

DIMENSIONS in millimeters (inches)









Lead assignments

MOSFET	<u>IGBT</u>
1 - Gate	1 - Gate
2 - Drain	2 - Collector
3 - Source	3 - Emitter
4 - Drain	4 - Collector

Notes

- (1) Dimension and tolerancing per ASME Y14.5M-1994
- (2) Controlling dimension: millimeter
- (3) Outline conforms to JEDEC® outline TO-274AA

Legal Disclaimer Notice



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